IN THE ABSTRACT

In the abstract, line 16, after the period, add the following sentence:

-Additionally, a memory device switchable between a patterned and a patternless addressing scheme is provided.-

IN THE CLAIMS

Please add claims 59-61 as follows:

59. (New) A memory device, comprising:

a memory array;

control logic operatively connected to the memory array, the control logic for selecting between a unpatterned pipeline and a patterned burst data pattern for accessing the memory array; and

switching circuitry for switching between a first pathway and a second pathway depending on which of said pipeline scheme and said burst scheme is selected.

60. (New) A memory device, comprising:

a memory array operable in a burst or a pipeline mode of operation;

control logic for selecting between the burst or the pipeline mode of operation; and

switching circuitry for switching between a first, burst data pathway and a second, pipeline data pathway depending on which of the burst or pipeline modes of operation is selected.

61. (New) A dynamic random access memory, comprising:

a plurality of addressable memory arrays;

a column address decoder for receiving an external column address;

control logic for selecting between a burst or a pipeline mode of operation based;

switching circuitry for switching between a burst pathway and a pipeline pathway depending on which of the burst or pipeline modes of operation is selected.